



## Si4427BDY vs. Si4427DY

**Description:** P-Channel, 30 V (D-S) MOSFET

**Package:** SOIC-8

**Pin Out:** Identical

**Part Number Replacements:**

Si4427BDY Replaces Si4427DY

Si4427BDY-E3 (Lead (Pb)-free version) Replaces Si4427DY

Si4427BDY-T1 Replaces Si4427DY-T1

Si4427BDY-T1-E3 (Lead (Pb)-free version) Replaces Si4427DY-T1

<b>ABSOLUTE MAXIMUM RATINGS</b> $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted					
Parameter	Symbol	Si4427BDY	Si4427DY	Unit	
Drain-Source Voltage	$V_{DS}$	- 30	- 30	V	
Gate-Source Voltage	$V_{GS}$	$\pm 12$	$\pm 12$		
Continuous Drain Current	$T_A = 25\text{ }^\circ\text{C}$	$I_D$	- 12.6	- 13.3	A
	$T_A = 70\text{ }^\circ\text{C}$		- 10.1	- 10.7	
Pulsed Drain Current	$I_{DM}$	- 50	- 50		
Continuous Source Current (MOSFET Diode Conduction)	$I_S$	- 2.5	- 2.5		
Power Dissipation	$T_A = 25\text{ }^\circ\text{C}$	$P_D$	2.5	3.0	W
	$T_A = 70\text{ }^\circ\text{C}$		1.6	1.9	
Operating Junction and Storage Temperature Range	$T_j$ and $T_{stg}$	- 55 to 150	- 55 to 150	$^\circ\text{C}$	
Maximum Junction-to-Ambient	$R_{thJA}$	50	42	$^\circ\text{C/W}$	

<b>SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted									
Parameter	Symbol	Si4427BDY			Si4427DY			Unit	
		Min	Typ	Max	Min	Typ	Max		
<b>Static</b>									
Gate-Threshold Voltage	$V_{G(th)}$	- 0.6		- 1.4	- 0.6			V	
Gate-Body Leakage	$I_{GSS}$			$\pm 100$			$\pm 100$	nA	
Zero Gate Voltage Drain Current	$I_{DSS}$			- 1			- 1	$\mu\text{A}$	
On-State Drain Current	$V_{GS} = - 10\text{ V}$	$I_{D(on)}$	- 50		- 50			A	
Drain-Source On-Resistance	$V_{GS} = - 10\text{ V}$	$r_{DS(on)}$		0.0088	0.0105		0.0086	0.0105	$\Omega$
	$V_{GS} = - 4.5\text{ V}$			0.0105	0.0125		0.0105	0.0125	
	$V_{GS} = - 2.5\text{ V}$			0.0150	0.0195		0.0165	0.0195	
Forward Transconductance		$g_{fs}$	44			40		S	
Diode Forward Voltage		$V_{SD}$	- 0.8	- 1.2	- 0.8	- 1.2		V	
<b>Dynamic</b>									
Total Gate Charge		$Q_g$	47.2	70		47	70	nC	
Gate-Source Charge		$Q_{gs}$	9.5			20			
Gate-Drain Charge		$Q_{gd}$	16.6			8.3			
<b>Switching</b>									
Turn-On Time		$t_{d(on)}$		12	20		16	25	ns
		$t_r$		15	25		12	20	
Turn-Off Time		$t_{d(off)}$		242	360		220	330	
		$t_f$		110	165		70	110	
Source-Drain Reverse Recovery Time		$t_{rr}$		70	110		50	80	

Specification comparisons are supplied as a courtesy to compare two devices and do not constitute a commercial product datasheet or any guarantee of identical performance. Designers should refer to the appropriate datasheets of the same number for guaranteed specification limits.